

General Description:

The LWT1H04AD5 uses advanced SGT technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications. The package form is PDFN5*6-8L, which accords with the ROHS standard and Halogen Free standard.

Features:

- Fast Switching
- Low Gate Charge and $R_{DS(ON)}$
- Low Reverse transfer capacitances

Applications:

- DC-DC Converter
- Portable Equipment
- Power Management

100% DVDS Tested

100% Avalanche Tested


Package Marking and Ordering Information:

Marking	Part Number	Package	Packing	Qty.
T1H04A/LW D5/D.C.	LWT1H04AD5	PDFN5*6-8L	Reel	5000 Pcs

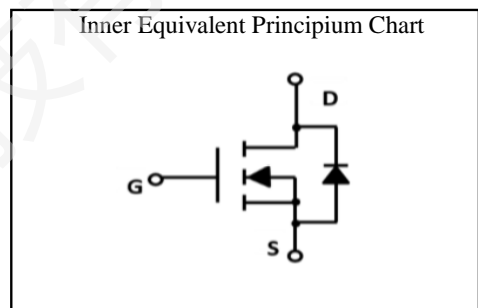
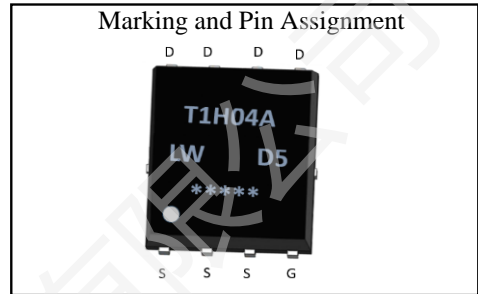
Absolute Maximum Ratings:

Symbol	Parameter	Value	Units
V_{DSS}	Drain-to-Source Voltage	100	V
I_D	Continuous Drain Current	$T_C=25^\circ\text{C}$	130
	Continuous Drain Current	$T_C=100^\circ\text{C}$	82
I_{DM}^{a1}	Pulsed Drain Current	520	A
E_{AS}^{a2}	Single pulse avalanche energy	126	mJ
V_{GS}	Gate-to-Source Voltage	± 20	V
P_D	Power Dissipation	132	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	150, -55 to 150	$^\circ\text{C}$
T_L	Maximum Temperature for Soldering	260	$^\circ\text{C}$

Thermal Characteristics:

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.95	$^\circ\text{C}/\text{W}$
$R_{\theta JA}^{a3}$	Thermal Resistance, Junction-to-Ambient	55	$^\circ\text{C}/\text{W}$

V_{DSS}	100	V
I_D	130	A
P_D	132	W
$R_{DS(ON) \text{ TYPE}}$	3.4	$\text{m}\Omega$



Electrical Characteristic ($T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified):

Static Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	100	--	--	V
I_{DSS}	Drain to Source Leakage Current	$V_{DS}=100V, V_{GS}=0V$	--	--	1.0	μA
$I_{GSS(F)}$	Gate to Source Forward Leakage	$V_{GS}=+20V, V_{DS}=0V$	--	--	100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	$V_{GS}=-20V, V_{DS}=0V$	--	--	-100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.3	1.8	2.3	V
$R_{DS(ON)1}$	Drain-to-Source On-Resistance	$V_{GS}=10V, I_D=20A$	--	3.4	4.1	$m\Omega$
$R_{DS(ON)2}$	Drain-to-Source On-Resistance	$V_{GS}=4.5V, I_D=10A$	--	4.0	6.0	$m\Omega$

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
C_{iss}	Input Capacitance	$V_{GS}=0V$ $V_{DS}=50V$ $f=1.0MHz$	--	4058	--	pF
C_{oss}	Output Capacitance		--	1406	--	
C_{rss}	Reverse Transfer Capacitance		--	27	--	
R_G	Gate resistance	$V_{GS}=0V, V_{DS}=0V, f=1MHz$	--	0.75	--	Ω

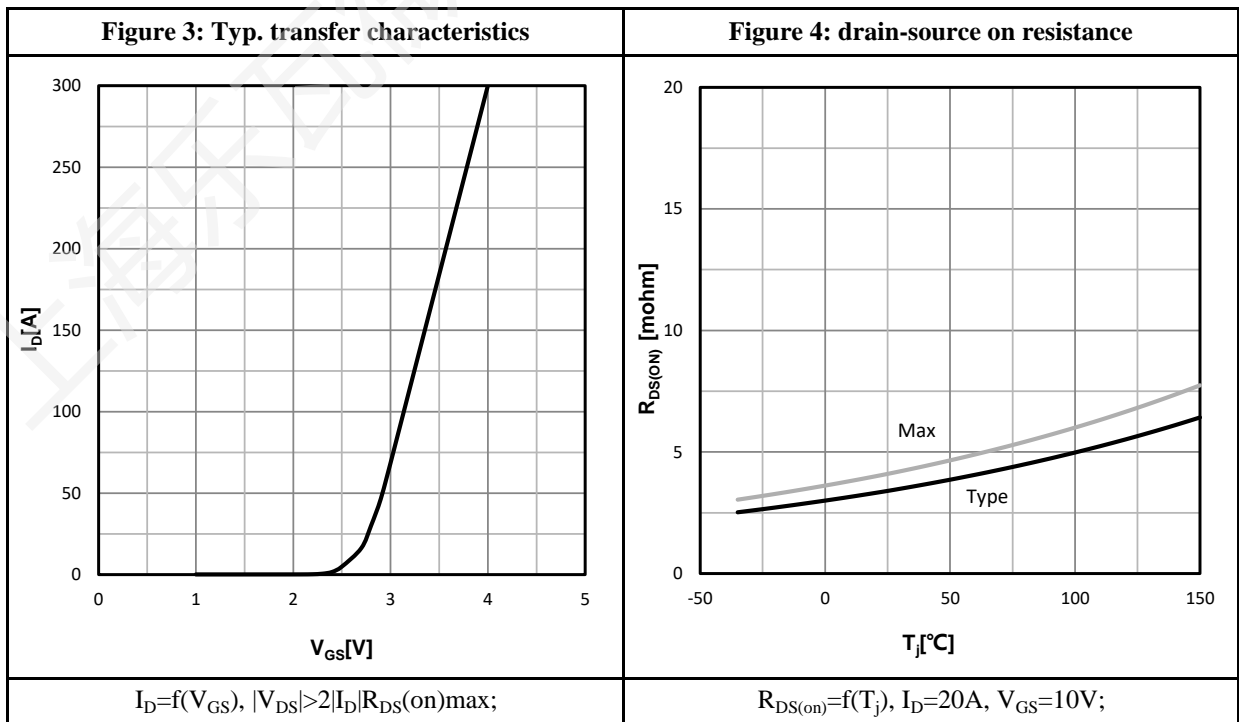
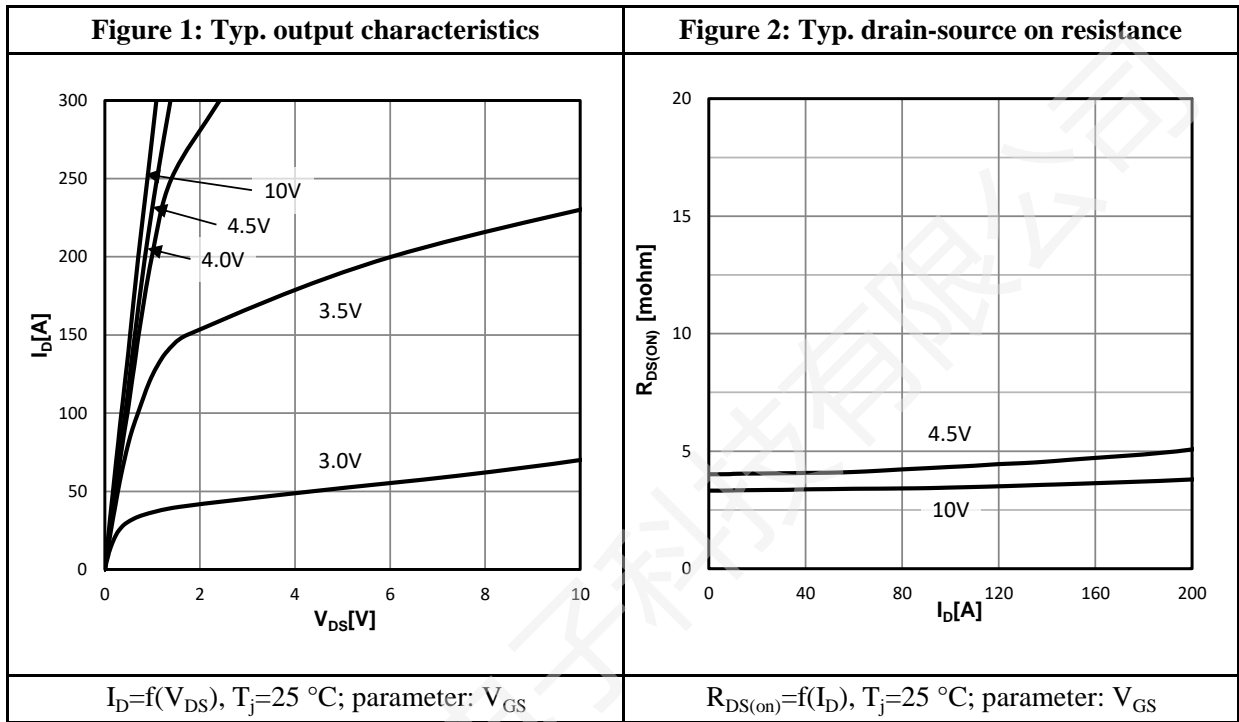
Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	$I_D=20A$ $V_{DS}=50V$ $V_{GS}=10V$ $R_G=5.0\Omega$	--	25	--	ns
t_r	Rise Time		--	33	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	95	--	
t_f	Fall Time		--	75	--	
Q_g	Total Gate Charge	$V_{GS}=10V$ $V_{DS}=50V$ $I_D=20A$	--	69	--	nC
Q_{gs}	Gate Source Charge		--	11	--	
Q_{gd}	Gate Drain Charge		--	14	--	

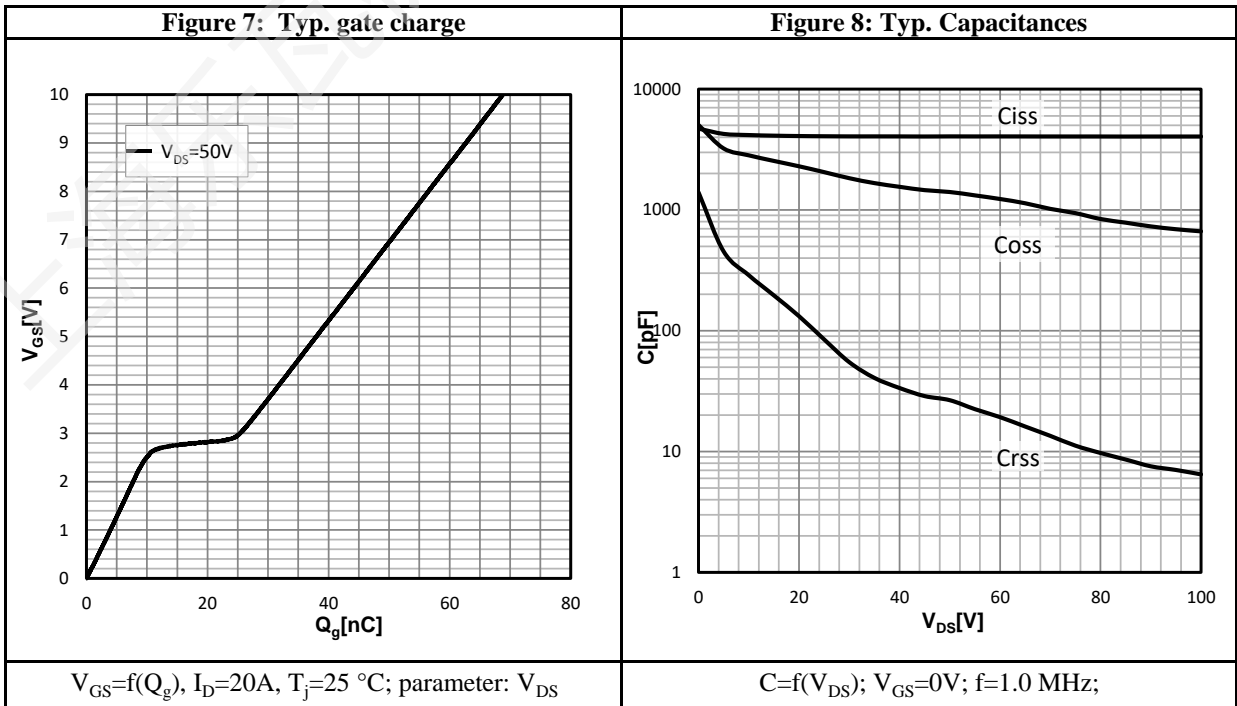
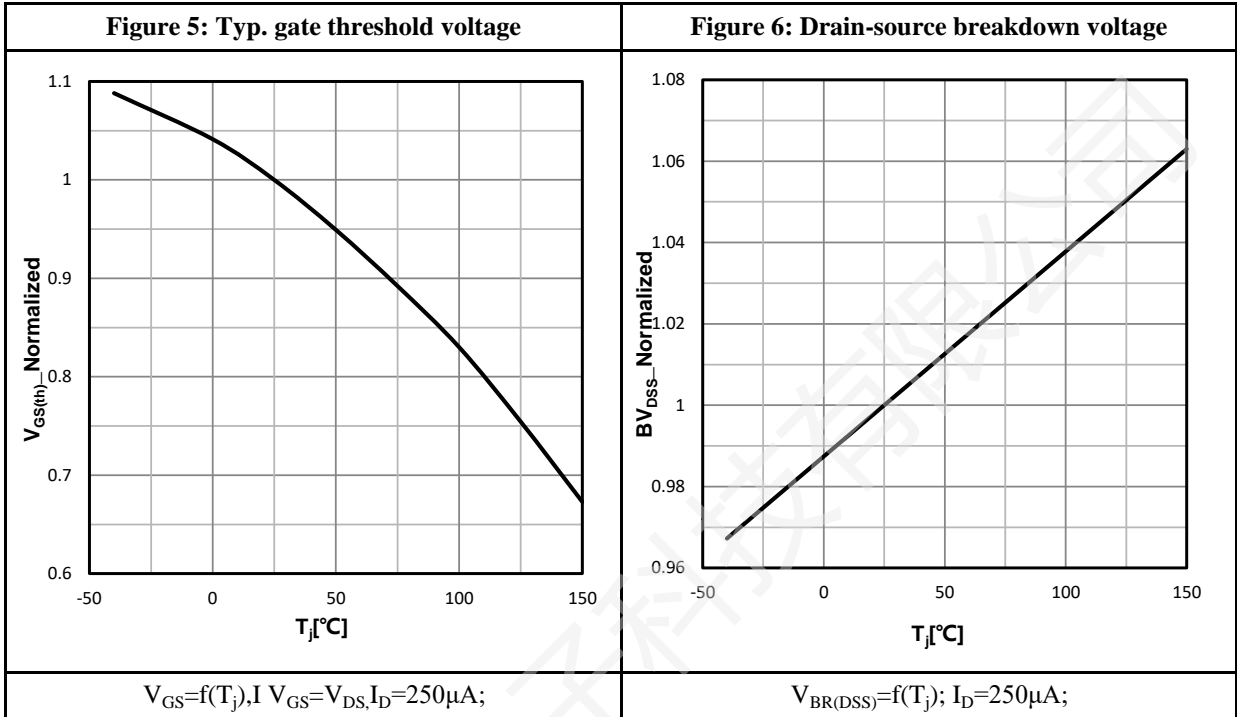
Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
I_S	Diode Forward Current	$T_C=25\text{ }^\circ\text{C}$	--	--	130	A
V_{SD}	Diode Forward Voltage	$I_S=20A, V_{GS}=0V$	--	--	1.2	V
t_{rr}	Reverse Recovery Time	$I_S=20A, V_{DD}=50V$ $dI/dt=100A/\mu s$	--	90	--	ns
Q_{rr}	Reverse Recovery Charge		--	180	--	nC

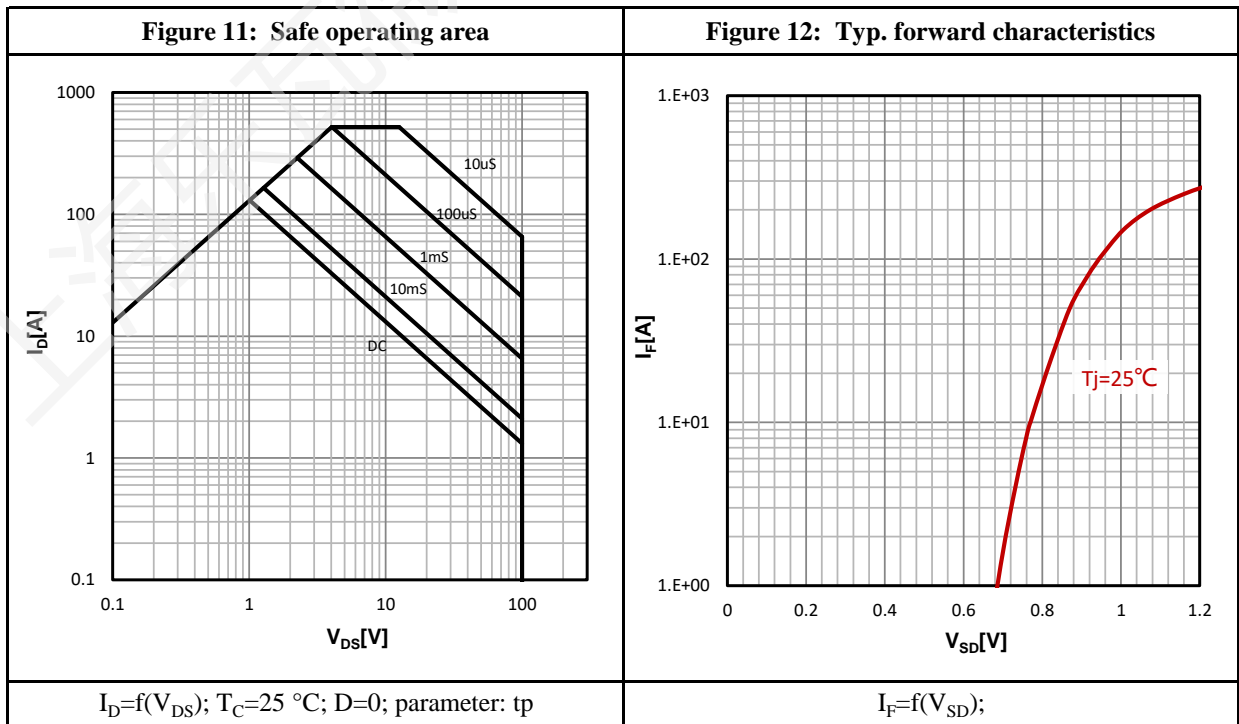
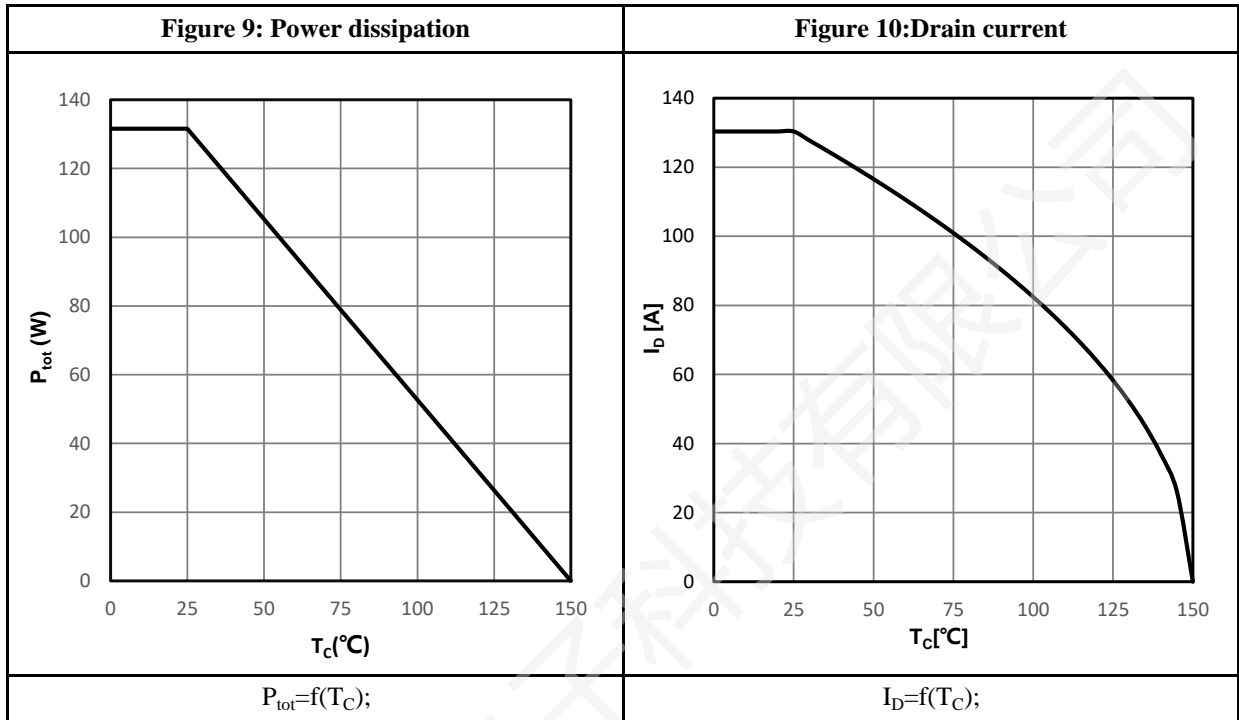
a1: Repetitive rating; pulse width limited by maximum junction temperature

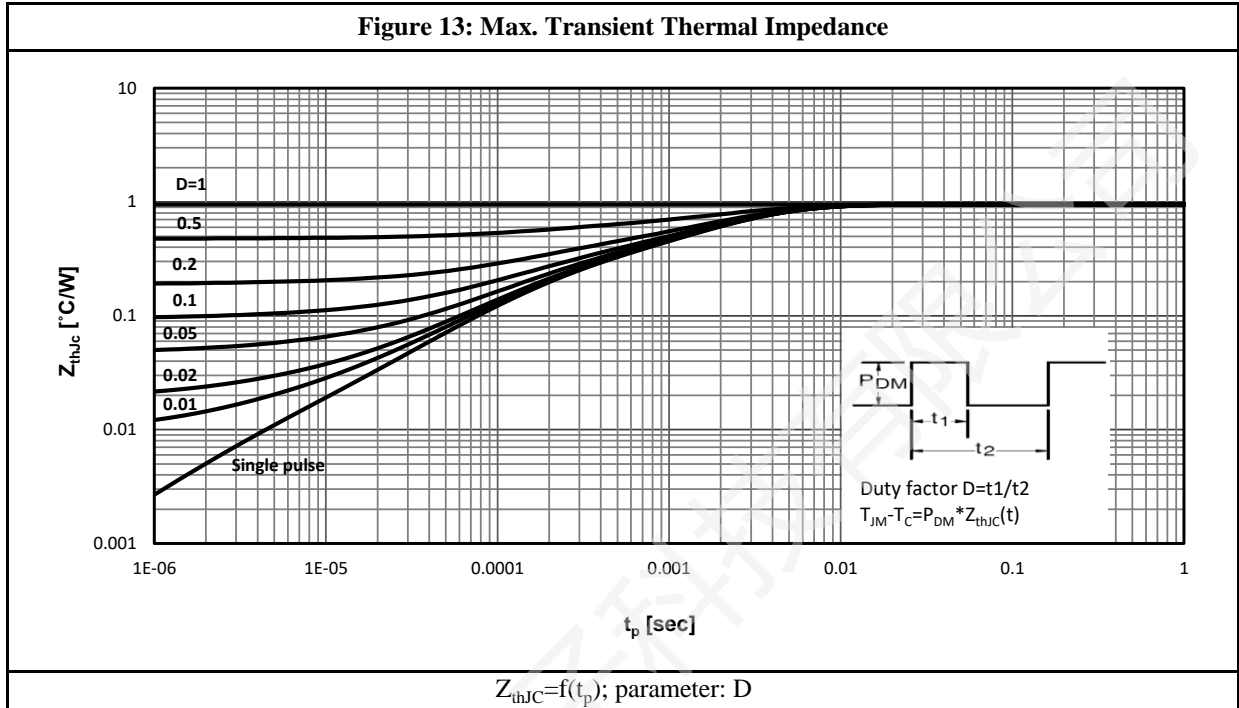
a2: $V_{DD}=50V, L=0.1mH, R_G=25\Omega$, Starting $T_j=25\text{ }^\circ\text{C}$

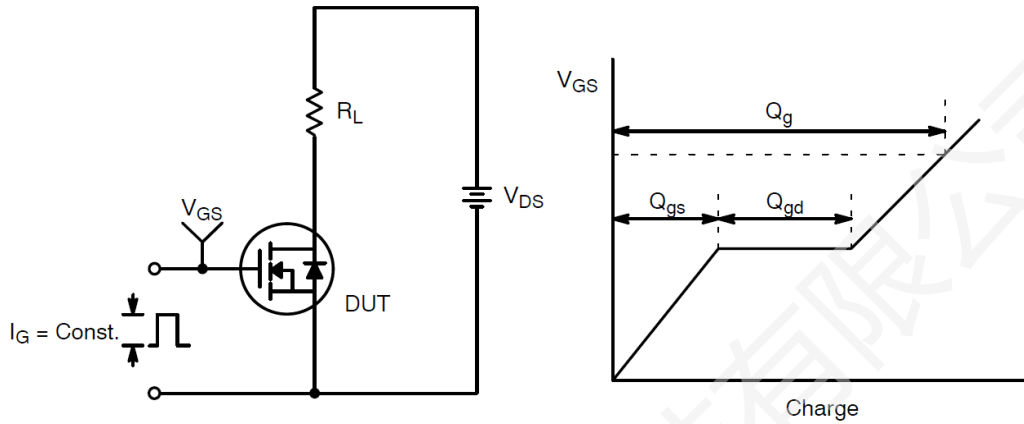
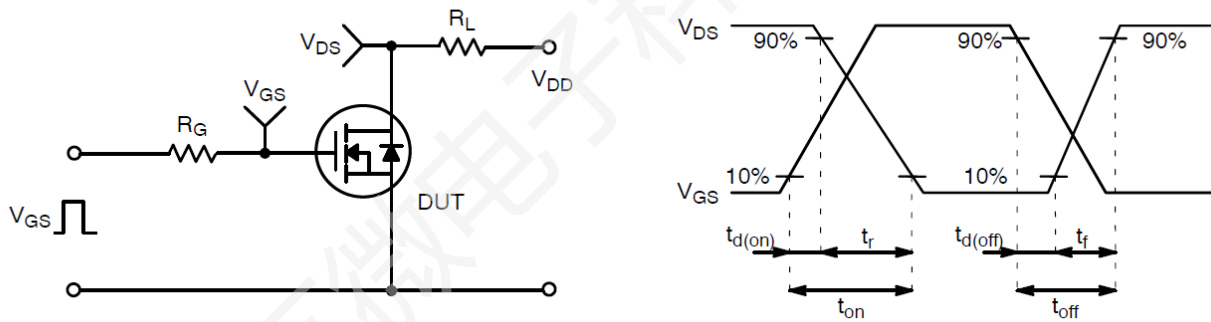
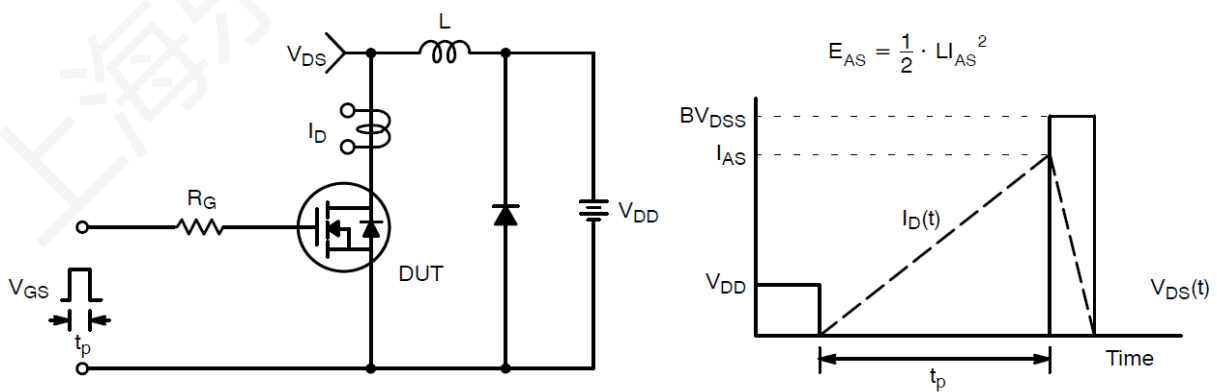
a3: Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection.

Characteristics Curve:


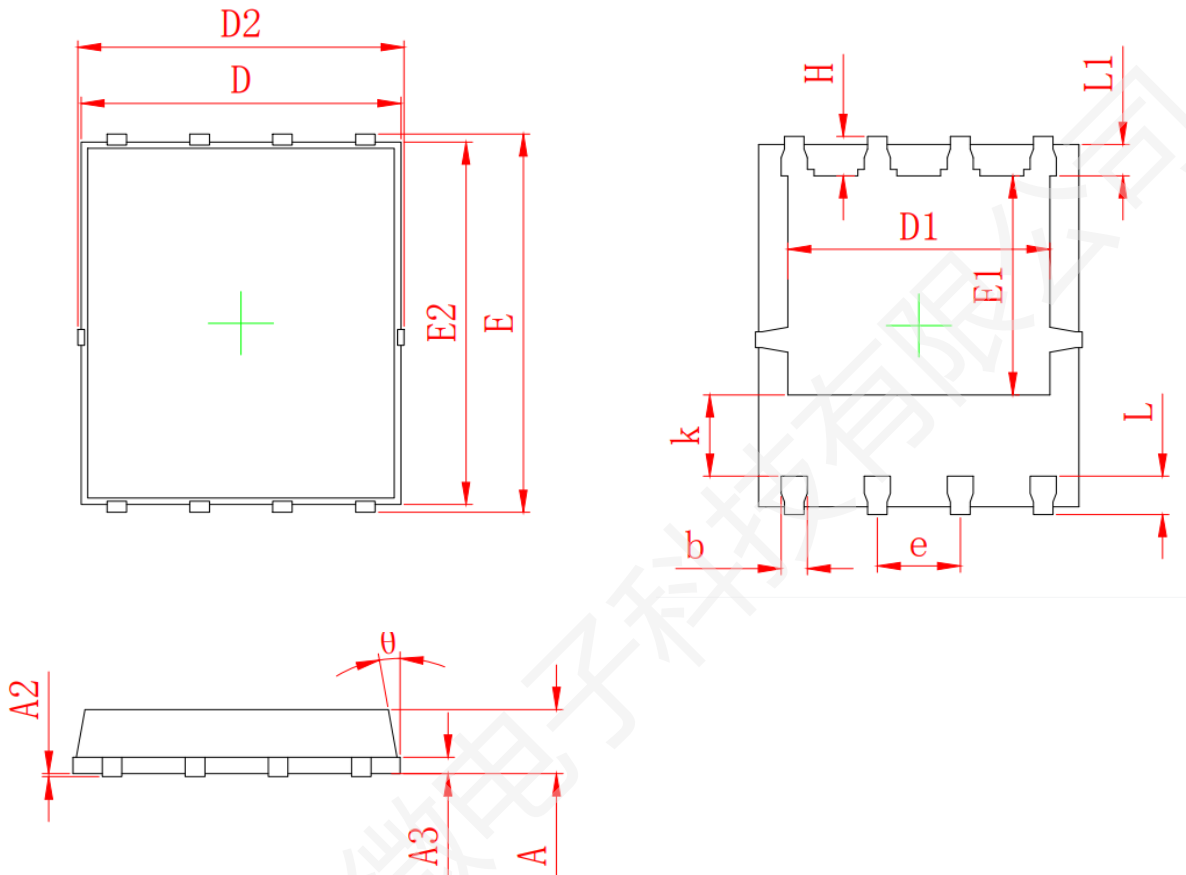






Test Circuit & Waveform:

Figure 14: Gate Charge Test Circuit & Waveform

Figure 15: Resistive Switching Test Circuit & Waveforms

Figure 16: Unclamped Inductive Switching Test Circuit & Waveforms

Package Outline:



Symbol	MILLIMETER	
	Min	Max
A	0.900	1.200
A1	0.254 REF	
A2	0~0.050	
D	4.824	4.976
D1	3.910	4.110
D2	4.944	5.076
E	5.924	6.076
E1	3.375	3.575
E2	5.674	5.826
b	0.350	0.450
e	1.270 TYP	
L	0.534	0.686
L1	0.424	0.576
k	1.190	1.390
H	0.549	0.701
θ	8°	12°

Revision History:

Revison	Date	Descriptions
Rev 1.2	Nov.2024	“Typical Performance Characteristics” Update
Rev 1.1	June.2024	“Electrical Characteristics” Update
Rev 1.0	Dec.2022	Initial Version

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